NSN 5961-01-330-9266

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View Online at https://aerobasegroup.com/nsn/5961-01-330-9266 **Inclosure Material:** Metal **Overall Length:** Between 0.180 inches and 0.210 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.209 inches and 0.230 inches **Function For Which Designed:** Phototransistor **End Application:** 1240-00-470-2156 range finder, fire control **Internal Configuration:** Junction contact **Electrode Internally-electrically Connected To Case:** Collector **Response Time:** 0.9 microseconds **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 collector to base voltage, dc and 50.0 collector to emitter voltage, dc and 7.0 emitter to collector voltage, dc **Power Rating Per Characteristic:** 250.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:**

Demilitarization:

Yes - demil/mli

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